

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

2 Priority Application Serial No. 08/710,353
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4 Inventor Pai-Hung Pan
5 Assignee Micron Technology, Inc.
6 Priority Group Art Unit 1107
7 Priority Examiner B. Mee
8 Attorney's Docket No. MI22-898
9 Title: Semiconductor Processing Methods of Forming a Conductive Gate and Line

7 PRELIMINARY AMENDMENT

8 To: Box PATENT APPLICATION
9 Assistant Commissioner for Patents
10 Washington, D.C. 20231

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14 Sir:

15 Applicant preliminarily amends as follows:

17 AMENDMENTS

18 In the Specification

19 At p. 1 before the "Technical Field" section, please insert the
20 following:

21 --RELATED PATENT DATA

22 This patent resulted from a continuation application of U.S. Patent
23 Application Serial No. 08/710,353, filed September 17, 1996, entitled
24 "Semiconductor Processing Methods of Forming a Conductive Gate and